



N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{(BR)DSS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)	
75	0.0076 at V _{GS} = 10 V	90 ^d	58	

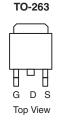
FEATURES

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_q and UIS Tested

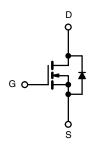


APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- Industrial



Ordering Information: SUM90N08-7m6P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _C = 25 °C, unless oth	erwise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	75	V	
Gate-Source Voltage		V _{GS}	± 20	7 v	
Continuous Drain Current (T _{.1} = 175 °C)	T _C = 25 °C	1-	90 ^d		
Continuous Drain Current (1) = 175 C)	T _C = 70 °C	I _D	81] _A	
Pulsed Drain Current		I _{DM}	200	7	
Avalanche Current		I _{AS}	50	1	
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D.	150 ^b	w	
	T _A = 25 °C ^c	$ P_D$ $-$	3.75		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1			

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

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SUM90N08-7m6P

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SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			I				
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	75			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.8		4.8		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
		V_{DS} = 75 V, V_{GS} = 0 V, T_J = 125 °C			50		
		V_{DS} = 75 V, V_{GS} = 0 V, T_J = 150 °C			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	70			Α	
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$		0.0063	0.0076	Ω	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C		0.0108	0.0130		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 30 A		55		S	
Dynamic ^b							
Input Capacitance	C _{iss}			3528		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		470			
Reverse Transfer Capacitance	C _{rss}			178			
Total Gate Charge ^c	Q_g			58	90	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 38 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		21			
Gate-Drain Charge ^c	Q_{gd}			16			
Gate Resistance	R _g	f = 1 MHz		1.8	3.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			21	35		
Rise Time ^c	t _r	$V_{DD} = 38 \text{ V, R}_{L} = 3.1 \Omega$ $I_{D} \cong 12.5 \text{ A, V}_{GEN} = 10 \text{ V, R}_{g} = 1 \Omega$		15	25	ns	
Turn-Off Delay Time ^c	t _{d(off)}			32	55		
Fall Time ^c	t _f			10	20		
Source-Drain Diode Ratings and Ch	aracteristics 7	_C = 25 °C ^b		•			
Continuous Current	Is				83		
Pulsed Current	I _{SM}				200	Α	
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V		0.85	1.5	V	
Reverse Recovery Time	t _{rr}			61	100	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 75 A, di/dt = 100 A/μs		2.7	4.5	Α	
Reverse Recovery Charge	Q _{rr}			83	140	nC	

Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

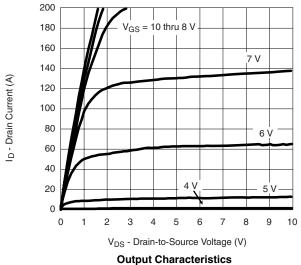
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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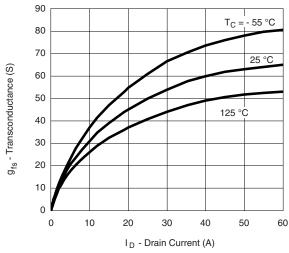
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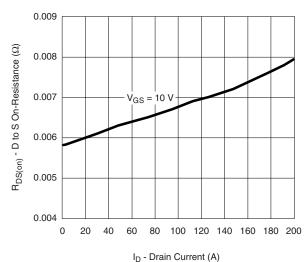
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



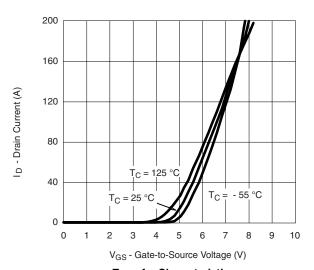




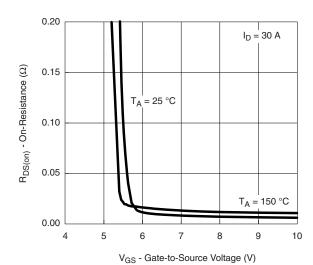
Transconductance



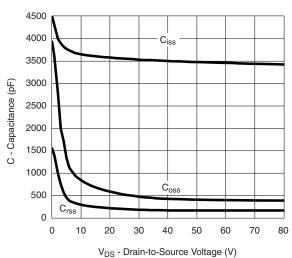
On-Resistance vs. Drain Current



Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage vs. Temperature



VDS - Diam-to-Source voltage (V)

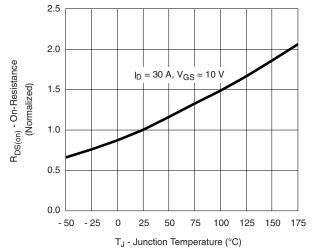
Capacitance

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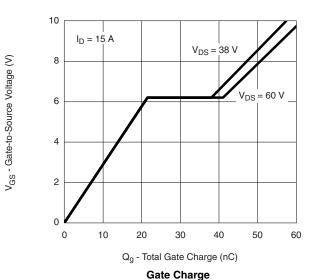
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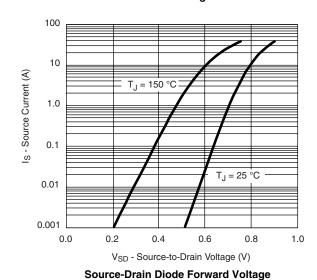
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



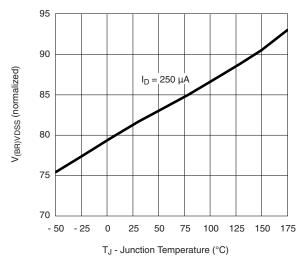
On-Resistance vs. Junction Temperature



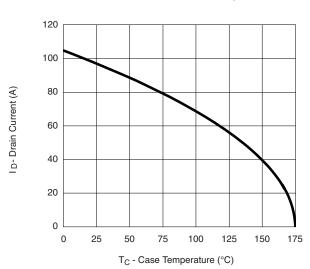


1.0 0.5 V_{GS(th)} Variance (V) 0.0 $I_D = 5 \text{ mA}$ - 0.5 - 1.0 $I_D = 250 \, \mu A$ - 1.5 - 2.0 - 50 - 25 50 75 100 125 150 175 0 25 T_J - Junction Temperature (°C)

Threshold Voltage



On-Resistance vs. Junction Temperature

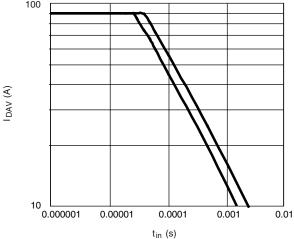


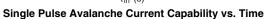
Maximum Drain Current vs. Case Temperature

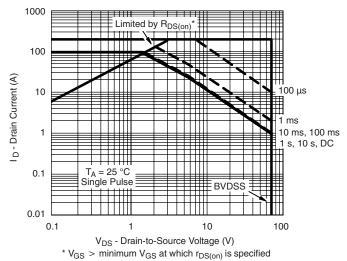


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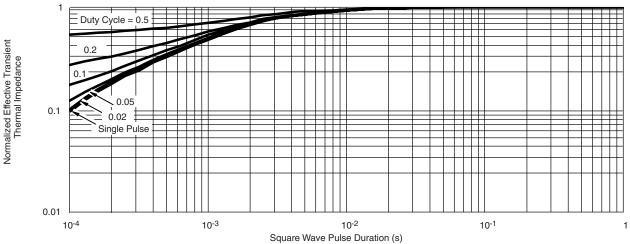
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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